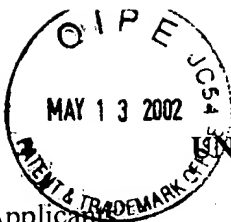


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UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Kalnitsky, et al.

Atty Docket: 60305-307201

Application No:

09/882,538

Group Art Unit:

2811

Filed: June 15, 2001

Title: **METHOD FOR FORMING A SUPER SELF-ALIGNED HETEROJUNCTION BIPOLAR TRANSISTOR**

Commissioner of Patents
Washington, D.C. 20231

RESPONSE TO OFFICE ACTION DUE 5/15/02

Dear Sir:

In response to the Office Action mailed February 15, 2002, please enter the following amendments and consider the following remarks

In the claims

Please amend the claims as follows:

1. (Amended) A method for forming a super self-aligned bipolar transistor, comprising the steps of:

providing a semiconductor substrate having a buried collector region;

providing multiple layers above said collector region;

providing an emitter window mask above said multiple layers;

providing three vertical etchings of said multiple layers;

providing a doping of said collector region wherein the doped collector region is determined by the emitter window mask;

providing a horizontal etching of one of said multiple layers, wherein the step of providing a horizontal etching determines that the dimensions of the base region are wider than the dimensions of the doped collector region and the emitter region;

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01 FC:102

84.00 OP

02 FC:103

54.00 OP

SV: 249093 v01 03/06/2002

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5/30/02
Smith